

In the Claims:

Please amend claims 1 and 15. Please add new claims 21 and 22. The claims are as follows:

1. (Currently Amended) A method ~~for testing a DDR DRAM having a test mode and an operational mode~~, comprising in the order recited:

- (a) placing said a DDR DRAM having a test mode and an operational mode in test mode;
- (b) issuing a bank activate command to select and bring up a wordline selected for write of said DDR DRAM;
- (c) writing with auto-precharge, a test pattern to cells of said DDR DRAM;
- (d) repeating steps (b) and (c) until all wordlines for write have been selected;
- (e) issuing a bank activate command to select and bring up a wordline selected for read of said DDR DRAM;
- (f) reading with auto-precharge, the stored test pattern from cells of said DDR DRAM;
- and
- (g) repeating steps (e) and (f) until all wordlines for read have been selected.

2. (Original) The method of claim 1, wherein each of steps (b), (c), (e) and (f) each take one clock cycle.

3. (Original) The method of claim 1, further including before step (a), the step of heating said DDR DRAM to a predetermined temperature.

4. (Original) The method of claim 1, wherein said DDR DRAM is operating at a clock frequency below about one MHz in said test mode.

5. (Original) The method of claim 1, wherein an amount of elapsed time between writing to and reading from a storage cell accessible by a particular wordline and bitline combination does not exceed a retention time specification of said storage cell.

6. (Original) The method of claim 1, wherein peripheral logic circuits of said DDR DRAM are adapted to execute a write burst enable and a column address command one clock cycle earlier in test mode than in operational mode, adapted to execute an auto-precharge enable one-half clock cycle earlier in test mode than in operational mode, and having a column address latency of one clock cycle in test mode and two or three clock cycles in operational mode.

7. (Original) The method of claim 1, wherein:

said DDR DRAM is adapted to initiate, in a timed auto-precharge mode of said test mode, a precharge immediately after a falling edge of a clock cycle; and

said DDR DRAM is adapted to, in a non-timed auto-precharge mode of said test mode, to start an auto-precharge asynchronously after the falling edge of a clock cycle and after a timer allows enough time for a write-back to said DDR DRAM.

8. (Withdrawn) A DDR DRAM having a low frequency and a high frequency operating mode, comprising:

a multiplicity of storage cells arranged in an array, each storage cell accessible by a wordline and a bitline; and

wherein peripheral logic circuits of said DDR DRAM are adapted to execute a write burst enable and a column address command one clock cycle earlier in low frequency operating mode than in high frequency operating mode, adapted to execute an auto-precharge enable one-half clock cycle earlier in low frequency operating mode than in high frequency operating mode, and having a column address latency of one clock cycle in test mode and two or three clock cycles in operational mode.

9. (Withdrawn) The DDR DRAM of claim 8, wherein said DDR DRAM is operating at a clock frequency below about 33 MHz in low frequency mode and at a clock frequency above about 33 MHz in high frequency mode.

10. (Withdrawn) The DDR DRAM of claim 8, wherein writing to a particular storage cell takes two clock cycles in low frequency operational mode and five clock cycles in high frequency operational mode.

11. (Withdrawn) The DDR DRAM of claim 10, wherein said DDR DRAM, during writing to said particular storage cell in low frequency mode is responsive to a bank activate command during a first clock cycle and responsive to a write with auto-precharge command during a second clock cycle.

12. (Withdrawn) The DDR DRAM of claim 10, wherein said DDR DRAM, during reading from said particular storage cell in low frequency mode is responsive to a bank activate command during a first clock cycle, responsive to a write command during a second clock cycle and responsive to a precharge command during a fifth clock cycle.

13. (Withdrawn) The DDR DRAM of claim 8, wherein reading from a particular storage cell takes four clock cycles in both in low and high frequency operational modes.

14. (Withdrawn) The DDR DRAM of claim 8, wherein:

said DDR DRAM is adapted to initiate, in a timed auto-precharge mode of low frequency operational mode, a precharge immediately after a falling edge of a clock cycle; and

said DDR DRAM is adapted to, in a non-timed auto-precharge mode of said test mode, to start an auto-precharge asynchronously after the falling edge of a clock cycle and after a timer allows enough time for a write-back to said DDR DRAM.

15. (Currently Amended) A computer system comprising a processor, an address/data bus coupled to said processor, and a computer-readable memory unit adapted to be coupled to said processor, said memory unit containing instructions that when executed by said processor implement a method for testing a DDR DRAM having a test mode and an operational mode, said method comprising the computer implemented steps of, in the order recited:

(a) placing said a DDR DRAM having a test mode and an operational mode in test mode;

(b) issuing a bank activate command to select and bring up a wordline selected for write of said DDR DRAM;

- (c) writing with auto-precharge, a test pattern to cells of said DDR DRAM;
 - (d) repeating steps (b) and (c) until all wordlines for write have been selected;
 - (e) issuing a bank activate command to select and bring up a wordline selected for read of said DDR DRAM;
 - (f) reading with auto-precharge, the stored test pattern from cells of said DDR DRAM;
- and
- (g) repeating steps (e) and (f) until all wordlines for read have been selected.

16. (Original) The system of claim 15, wherein each of steps (b), (c), (c) and (f) each take one clock cycle.

17. (Original) The method of claim 15, wherein an amount of elapsed time between writing to and reading from a storage cell accessible by a particular wordline and bitline combination does not exceed a retention time specification of said storage cell.

18. (Original) The system of claim 15, further including before step (a), the method step of heating said DDR DRAM to a predetermined temperature.

19. (Original) The system of claim 15, wherein said DDR DRAM is operating at a clock frequency below about one MHz in test mode.

20. (Original) The system of claim 15, wherein an amount of elapsed time between writing to and reading from a storage cell accessible by a particular wordline and bitline combination does not exceed a retention time specification of said storage cell.

21. (New) The method of claim 1, further including:

(f) comparing said test pattern to said stored test pattern.

22. (New) The system of 15, the method further including:

(f) comparing said test pattern to said stored test pattern.